IN THE CLAIMS

- (Original) A diffusion furnace for use in fabricating semiconductor devices, 1. the furnace comprising:
 - a support member;
 - a process chamber installed on the support member;
- a sealing member for sealing the process chamber from the outside, the sealing member being inserted between the support member and the process chamber; and
- a cooling system for cooling the sealing member, the cooling system including a first fluid passage in which a first fluid flows for cooling the sealing member, the first fluid passage being formed within the support member, and a second fluid passage in which a second fluid flows for cooling the sealing member when supplying the first fluid is interrupted, the second fluid passage being formed within the support member.
- (Original) The diffusion furnace of claim 1, wherein the cooling system 2. includes:
- a first supply conduit connected to a first inflow port formed at one end of the first fluid passage;
- a return conduit connected to a first outflow port formed at the other end of the first fluid passage;
- a temperature controller, to which the first supply conduit and the return conduit are connected, for controlling the temperature of the first fluid supplied to the first supply conduit;
- a second supply conduit connected to a second inflow port formed at one end of the second fluid passage; and
- an exhaust conduit connected to a second outflow port formed at the other end of the second fluid passage.
- (Original) The diffusion furnace of claim 1, wherein the sealing member is an 3. O-ring.
- (Original) The diffusion furnace of claim 1, wherein the first and second fluid 4. passages are substantially ring-shaped.

- 5. (Original) The diffusion furnace of claim 4, wherein the second fluid passage is formed substantially coplanar with the first fluid passage.
- 6. (Original) The diffusion furnace of claim 4, wherein the first fluid passage and the second fluid passage are disposed one over the other.
- 7. (Original) The diffusion furnace of claim 1, wherein the first fluid has a higher boiling point than the second fluid.
- 8. (Original) The diffusion furnace of claim 1, wherein the second fluid is cooling water.
- 9. (Original) The diffusion furnace of claim 1, wherein the first fluid is an organic liquid.
- 10. (Original) The diffusion furnace of claim 1, wherein the first fluid is ethylene glycol.
 - 11. (Withdrawn) A method for cooling a diffusion furnace, the method comprising:

providing said diffusion furnace which includes a process chamber located on a support chamber;

supplying a first fluid at a temperature controlled by a temperature controller to a first fluid passage formed in the support member;

shutting off a first supply pipe connected to the first fluid passage when an error occurs at the temperature controller; and

opening a second fluid passage connected to a second fluid passage disposed in the flange to supply a second fluid to the second fluid passage.

- 12. (Withdrawn) The method of claim 11, further comprising exhausting the second fluid from the second fluid passage to the outside.
- 13. (Withdrawn) The method of claim 11, wherein the second fluid is cooling water.

- 14. (Withdrawn) The method of claim 11, wherein the first fluid is glycol.
- 15. (Withdrawn) The method of claim 11, wherein the first and second fluid passages are substantially ring-shaped.
- 16. (Withdrawn) The method of claim 11, wherein the second fluid passage is formed substantially coplanar with the first fluid passage.
- 17. (Withdrawn) The method of claim 11, wherein the first fluid passage and the second fluid passage are disposed one over the other.
- 18. (Withdrawn) A method for cooling a diffusion furnace for fabricating semiconductor devices, the method comprising:

providing said diffusion furnace which includes a process chamber located on a support member;

supplying a first fluid at a temperature within a predetermined temperature range to a first fluid passage formed within said support member for cooling said support member during fabrication of said semiconductor devices;

shutting off the supply of the first fluid when the temperature of the first fluid is outside the predetermined temperature range; and

supplying a second fluid to a second fluid passage within the support member for cooling the support member to a temperature within the predetermined temperature range.

- 19. (Withdrawn) The method of claim 18, which further includes providing a sealing member, and sealing said process chamber from the outside with said sealing member.
- 20. (Withdrawn) The method of claim 18, wherein the scaling member comprises an O-ring.

- (Withdrawn) The method of claim 18, which further comprises exhausting the 21. second fluid from the second fluid passage to the outside.
- (Withdrawn) The method of claim 18, wherein the second fluid passage is 22. formed substantially coplanar with the first fluid passage.
- (Withdrawn) The method of claim 18, wherein the first fluid passage and the 23. second fluid passage are disposed one over the other.
- (New) The diffusion furnace of claim1, wherein the second fluid flows in the 24. second fluid passage when an error occurs at the temperature controller.
- (New) The diffusion furnace of claim 24, wherein the second fluid flows in 25. the second fluid passage in response to an electrical control signal.